

## **AMENDMENTS**

### **In the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listing of Claims:**

1. (Original) A manufacturing method of a transflective TFT-LCD panel, comprising the steps of:
  - forming a first conductive layer on a substrate;
  - defining the first conductive layer to form a gate;
  - forming a dielectric layer thereon;
  - forming a channel over the gate;
  - forming a photo-resist block;
  - forming a second conductive layer;
  - defining the second conductive to form a source and a drain over the gate, meanwhile, forming a photo-reflective layer on the photo-resist block;
  - forming a protection layer thereon;
  - defining the protection layer, forming a first opening on the drain allowing part of the drain to be exposed, and forming a second opening on the photo-reflective layer allowing part of the photo-reflective layer to be exposed; and
  - forming a transparent electrode electrically connected to the drain and the photo-reflective layer via the first and the second opening.

2. (Original) A manufacturing method according to claim 1, wherein a capacitor electrode set under the photo-resist block is formed during the step of defining the first conductive layer.

3. (Original) A manufacturing method according to claim 1, wherein the first conductive layer is a first metal layer.

4. (Original) A manufacturing method according to claim 1, wherein the substrate is a glass substrate.

5. (Original) A manufacturing method according to claim 1, wherein the photo-resist block is composed of positive photo-resist.

6. (Original) A manufacturing method according to claim 1, wherein the second conductive layer is a second metal layer.

7. (Original) A manufacturing method according to claim 1, wherein the transparent electrode is composed of indium-tin oxide (ITO).

8. (Original) A manufacturing method of a transflective TFT-LCD panel equipped with a transmissive area and a reflective area, comprising the steps of:

forming a thin film transistor and a capacitor electrode on the substrate, wherein a photo-reflective layer within the reflective area and a source and a drain of the thin film transistor are formed simultaneously; and

forming a transparent electrode within the transmissive area.

9. (Original) A manufacturing method according to claim 8, wherein the photo-reflective layer is formed largely above the capacitor electrode.

10. (Original) A manufacturing method according to claim 8, wherein a photo-resist block is formed on the capacitor electrode prior to the formation of the photo-reflective layer.

11. Canceled.

12. Canceled.